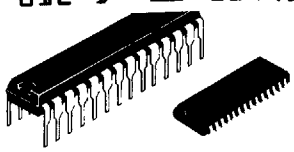


M5M5178P,J-35,-45,-55

65536-BIT (8192-WORD BY 8-BIT) CMOS STATIC RAM

MITSUBISHI (MEMORY/ASIC)

DESCRIPTION

This is a family of 8192 word by 8-bit static RAMs, fabricated with the high performance CMOS silicon gate MOS process and designed for high-speed application. These devices operate on a single 5V supply, and are directly TTL compatible.

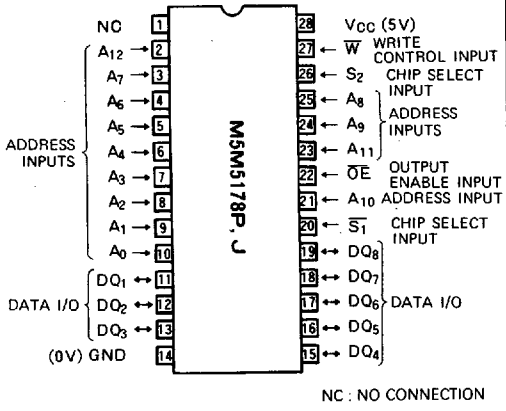
FEATURES

- Fast access time M5M5178-35 . . . . . 35ns (max.)
  M5M5178-45 . . . . . 45ns (max.)
  M5M5178-55 . . . . . 55ns (max.)
- Single +5V Power Supply
- Fully Static Operation: No Clocks, No Refresh
- Directly TTL Compatible: All Inputs and Outputs
- Three-State Outputs: OR-tie Capability
- Simple Memory Expansion by $\overline{S_1}$, S_2
- $\overline{OE}$ Prevents Data Contention in The I/O Bus
- Common Data I/O
- 300 mil package

APPLICATION

High speed memory system

PIN CONFIGURATION (TOP VIEW)



NC : NO CONNECTION

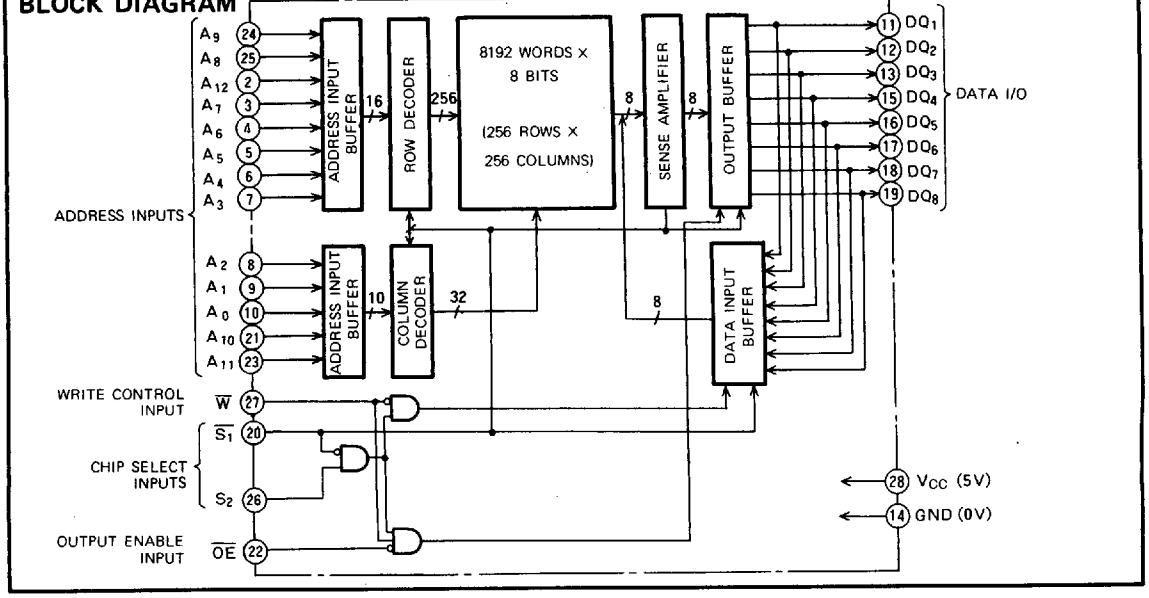
Outline 28P4Y (DIP)
28P0J (SOJ)

FUNCTION

The operation mode of the M5M5178 is determined by a combination of the device control inputs $\overline{S_1}$, S_2, $\overline{W}$ and $\overline{OE}$. Each mode is summarized in the function table. (see next page)

A write cycle is executed whenever the low level $\overline{W}$ overlaps with the low level $\overline{S_1}$ and the high level S_2. The address must be set up before the write cycle and must be stable during the entire cycle. The data is latched into a cell on the trailing edge of $\overline{W}$, $\overline{S_1}$ or S_2, whichever occurs first, requiring the set-up and hold time relative to these edge to be maintained. The output enable input $\overline{OE}$ directly controls the output stage. Setting the $\overline{OE}$ at a high level, the output stage is in a high-impedance state, and the data bus contention problem in the write cycle is eliminated.

BLOCK DIAGRAM



65536-BIT (8192-WORD BY 8-BIT) CMOS STATIC RAM

A read cycle is executed by setting $\overline{W}$ at a high level and $\overline{OE}$ at a low level while $\overline{S_1}$ and S_2 are in an active state ($\overline{S_1}$ = L, S_2 = H)

When setting $\overline{S_1}$ at a high level, the chip is in a non-selectable mode in which both reading and writing are disabled. In this mode, the output stage is in a high-impedance state, allowing OR-tie with other chips and memory expantion by $\overline{S_1}$. The power supply current is reduced as low as the stand-by current which is specified as I_{CC2} or I_{CC3}.

FUNCTION TABLE

$\overline{S_1}$	S_2	$\overline{W}$	$\overline{OE}$	Mode	DQ	I_{CC}
L	L	X	X	Non selection	high-impedance	Active
H	X	X	X	Non selection	high-impedance	Standby
L	H	L	X	Write	D_{IN}	Active
L	H	H	L	Read	D_{OUT}	Active
L	H	H	H		high-impedance	Active

ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Conditions	Ratings	Unit
V_{CC}	Supply voltage	With respect to GND	−0.3～7	V
V_I	Input voltage		−0.3～V_{CC}+0.3	V
V_O	Output voltage		0～V_{CC}	V
P_d	Power dissipation	Ta=25°C	1000	mW
T_{opr}	Operating temperature		−10～85	°C
T_{stg}	Storage temperature		−65～150	°C

DC ELECTRICAL CHARACTERISTICS (Ta=0～70°C, V_{CC}=5V±10%, unless otherwise noted)

Symbol	Parameter	Test conditions	Limits			Unit
			Min	Typ	Max	
V_{IH}	High input voltage		2.2		V_{CC}+0.3	V
V_{IL}	Low input voltage		−0.3		0.8	V
V_{OH}	High output voltage	I_{OH}=−4mA	2.4			V
V_{OL}	Low output voltage	I_{OL}=8 mA			0.4	V
I_I	Input current	V_I=0～V_{CC}			±1	μA
I_{OZH}	High level output current in off-state	$\overline{S_1}$=V_{IH} or S_2=V_{IL} or $\overline{OE}$=V_{IH} $V_{I/O}$=0～V_{CC}			1	μA
I_{OZL}	Low level output current in off-state				−1	μA
I_{CC1}	Active supply current	$\overline{S_1}$=V_{IL} or S_2=V_{IH} Output open Other inputs =V_{IH}			120	mA
I_{CC2}	Stand by supply current	S_2=V_{IL}, $\overline{S_1}$=V_{IH}, Other inputs=0～V_{CC}			25	mA
I_{CC3}	Stand by supply current	$\overline{S_1}$≧V_{CC}−0.2V Other inputs ≦0.2V or V_{CC}−0.2V			2	mA
C_i	Output capacitance (Ta=25°C) $\overline{S_1}$, S_2, $\overline{OE}$, $\overline{W}$	V_I=GND, V_i=25mVrms, f=1MHz			7	pF
	Output capacitance (Ta=25°C) A_0～A_{12}				6	pF
C_o	Outout capacitance (Ta=25°C)	V_O=GND, V_O=25mVrms, f=1MHz			8	pF

Note 1 Direction for current flowing into IC is indicated as positive (no mark)
2 Typical value is V_{CC}=5V, Ta=25°C

SWITCHING CHARACTERISTICS (T_a=0~70°C, V_{CC}=5V±10%, unless otherwise noted)

Read cycle

Symbol	Parameter	Limits									Unit
		M5M5178-35			M5M5178-45			M5M5178-55			
		Min	Typ	Max	Min	Typ	Max	Min	Typ	Max	
t_{CR}	Read cycle time	35			45			55			ns
$t_{a(A)}$	Address access time			35			45			55	ns
$t_{a(S1)}$	Chip select 1 access time			35			45			55	ns
$t_{a(S2)}$	Chip select 2 access time			20			25			30	ns
$t_{a(OE)}$	Output enable access time			15			20			25	ns
$t_{dis(S1)}$	Output disable time after $\overline{S_1}$ high			20			25			35	ns
$t_{dis(S2)}$	Output disable time after S_2 low			20			25			35	ns
$t_{dis(OE)}$	Output disable time after $\overline{OE}$ high			20			25			35	ns
$t_{en(S1)}$	Output enable time after $\overline{S_1}$ low	5			5			5			ns
$t_{en(S2)}$	Output enable time after S_2 high	3			3			3			ns
$t_{en(OE)}$	Output enable time after $\overline{OE}$ low	3			3			3			ns
$t_{v(A)}$	Data valid time after address change	3			3			3			ns

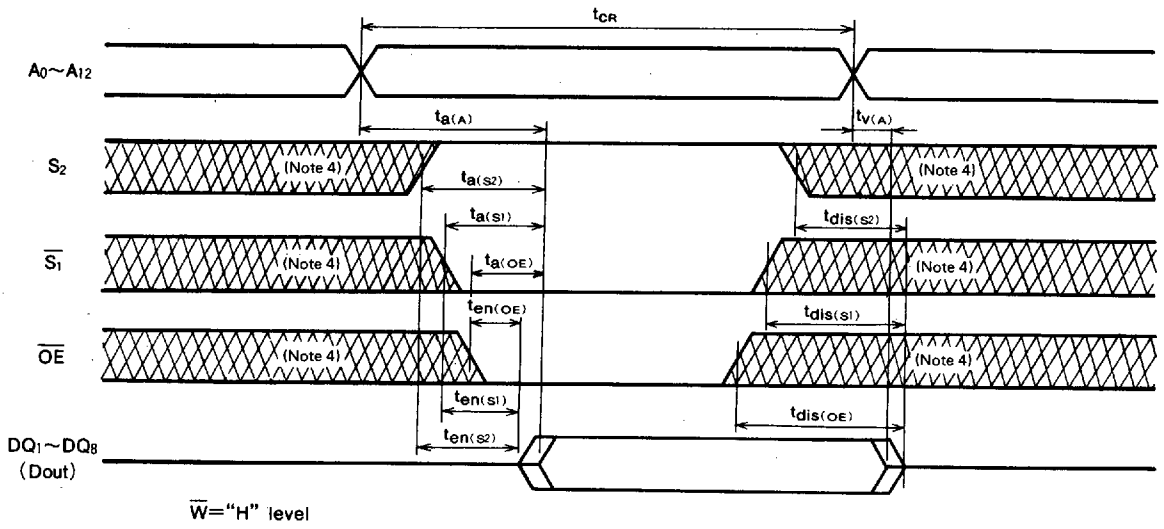
TIMING REQUIREMENTS (T_a=0~70°C, V_{CC}=5V±10%, unless otherwise noted)

Write cycle

Symbol	Parameter	Limits									Unit
		M5M5178-35			M5M5178-45			M5M5178-55			
		Min	Typ	Max	Min	Typ	Max	Min	Typ	Max	
t_{CW}	Write cycle time	35			45			55			ns
$t_{w(W)}$	Write pulse width	20			25			30			ns
$t_{su(A)}$	Address set up time	0			0			0			ns
$t_{su(S1)}$	Chip select 1 set up time	30			40			45			ns
$t_{su(S2)}$	Chip select 2 set up time	20			25			30			ns
$t_{su(D)}$	Data set up time	17			20			30			ns
$t_{h(D)}$	Data hold time	0			0			0			ns
$t_{rec(W)}$	Write recovery time	3			3			3			ns
$t_{dis(W)}$	Output disable time after $\overline{W}$ low			20			20			20	ns
$t_{dis(OE)}$	Output disable time after $\overline{OE}$ high			15			25			25	ns
$t_{en(W)}$	Output enable time after $\overline{W}$ high	0			0			0			ns
$t_{en(OE)}$	Output enable time after $\overline{OE}$ low	3			3			3			ns

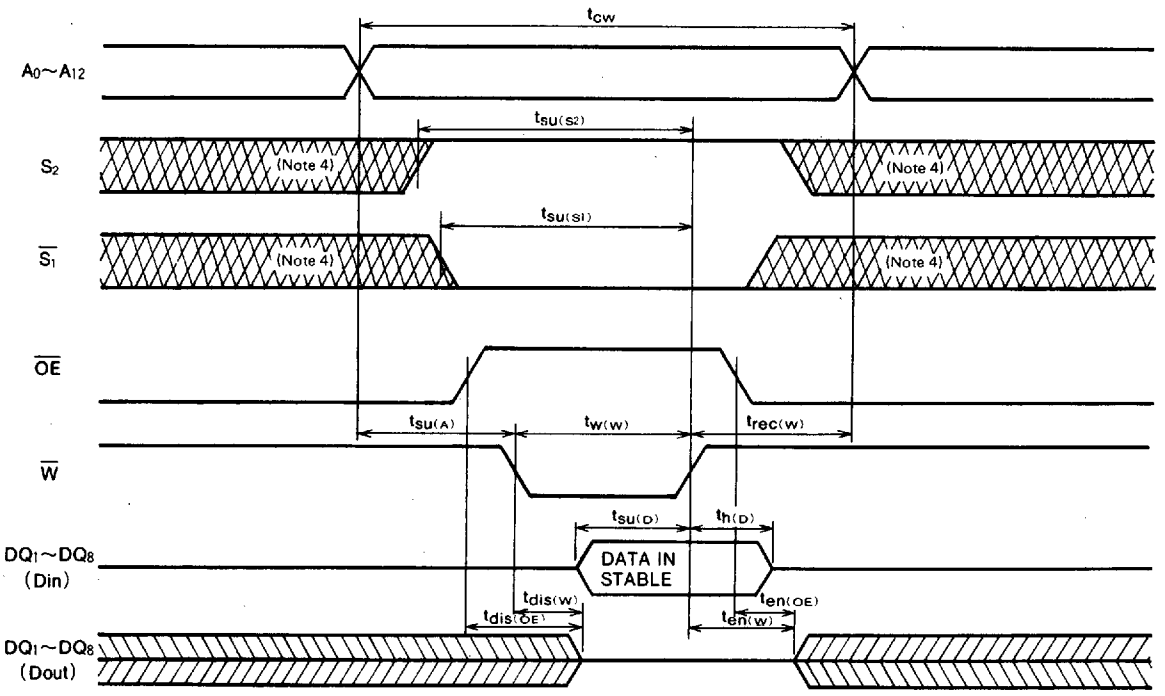
TIMING DIAGRAM

Read cycle

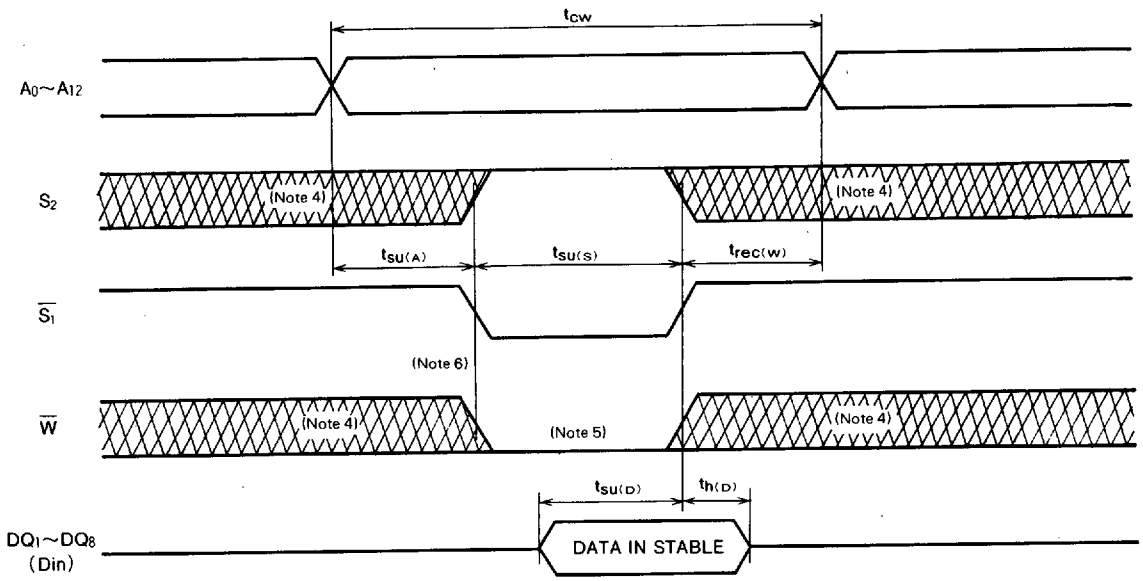


W=“H” level

Write cycle (W control)



Write cycle ($\overline{S}$ control)



CONDITIONS

Input pulse levels . . . . . 0 to 3V
Input rise and fall time 5ns
Input timing reference level 1.5V
Output timing reference level . . . . . 0.8V ~ 2V
Output loads . . . . . Fig. 1, Fig. 2

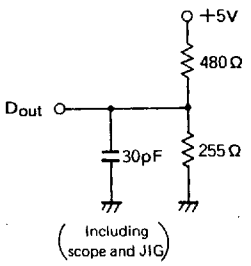


Fig. 1 Output load

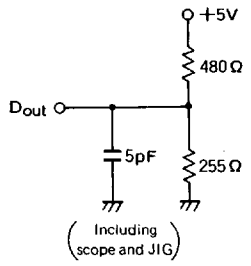


Fig. 2 Output load for t_{en} t_{dis}

Note 4: Hatching indicates the state is don't care.
5: Writing is executed while S_2 high overlaps $\overline{S_1}$ and $\overline{W}$ low.
6: If $\overline{W}$ goes low simultaneously with or prior to $\overline{S_1}$ low or S_2 high, the output remains in the high-impedance state.
7: Don't apply inverted phase signal externally when DQ pin is in output mode.